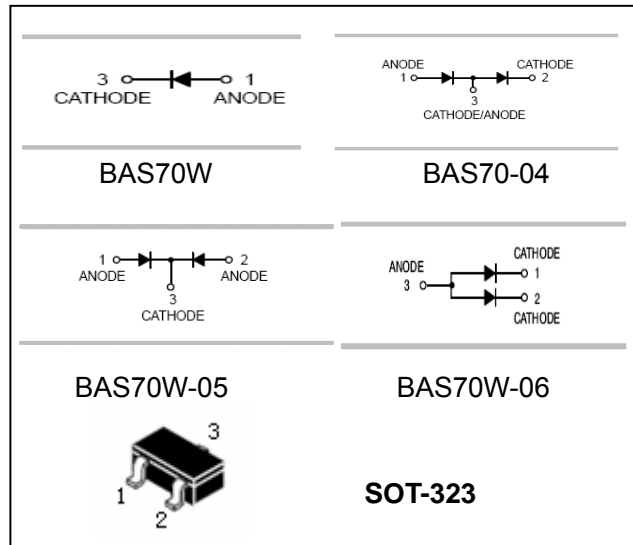


FEATURES

- Low Forward voltage drop.
- High breakdown voltage.
- Guard ring protected.
- Low capacitance.
- Very small SMD package.



APPLICATIONS

- For high speed switching applications.

ORDERING INFORMATION

Type No.	Marking	Package Code
BAS70W	K73	SOT-323
BAS70W-04	K74	SOT-323
BAS70W-05	K75	SOT-323
BAS70W-06	K76	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Repetitive Peak reverse voltage	V_{RRM}	70	V
Working peak reverse voltage	V_{RWM}		
Diode reverse voltage	V_R		
Forward continuous Current	I_F	70	mA
Non-Repetitive peak forward surge Current @t=1μs	I_{FS}	100	mA
Power Dissipation	P_d	200	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-65-+150	°C

Diode Semiconductor Korea

Surface Mount Schottky Barrier Diode

BAS70W/-04/-05/-06

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 10\mu A$	70		V
Reverse voltage leakage current	I_R	$V_R = 50V$		100	nA
Forward voltage	V_F	$I_F = 1.0mA$ $I_F = 15mA$		410 1000	mV
Diode capacitance	C_D	$V_R = 0V$ $f = 1MHz$		2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$ $R_L = 100\Omega$		5	nS

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

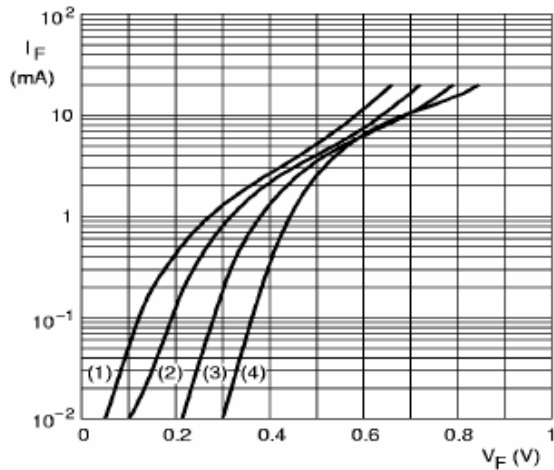


Fig.6 Forward current as a function of forward voltage; typical values.

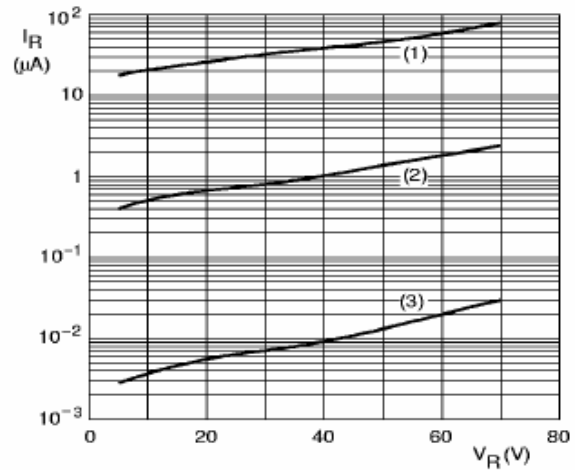


Fig.7 Reverse current as a function of reverse voltage; typical values.

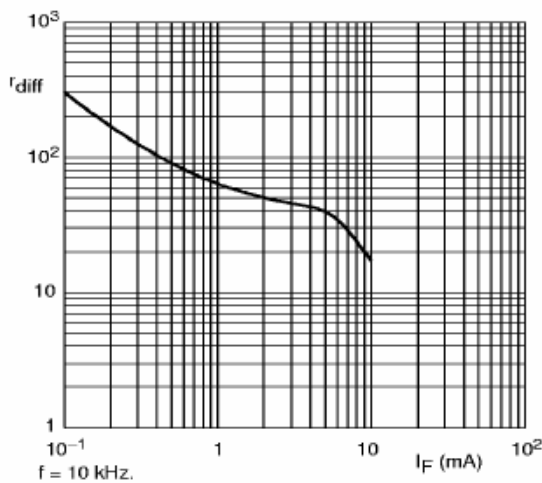


Fig.8 Differential forward resistance as a function of forward current; typical values.

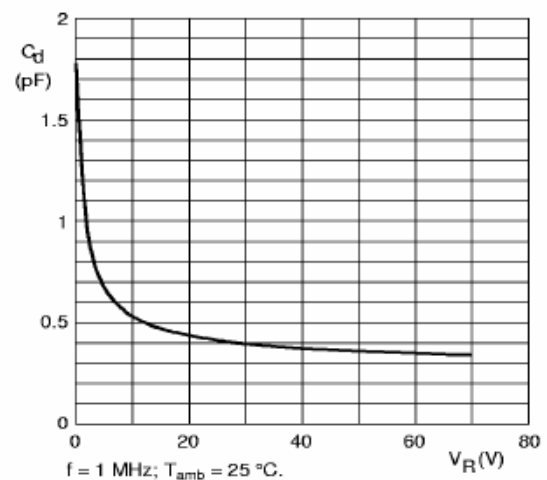


Fig.9 Diode capacitance as a function of reverse voltage; typical values.

Diode Semiconductor Korea

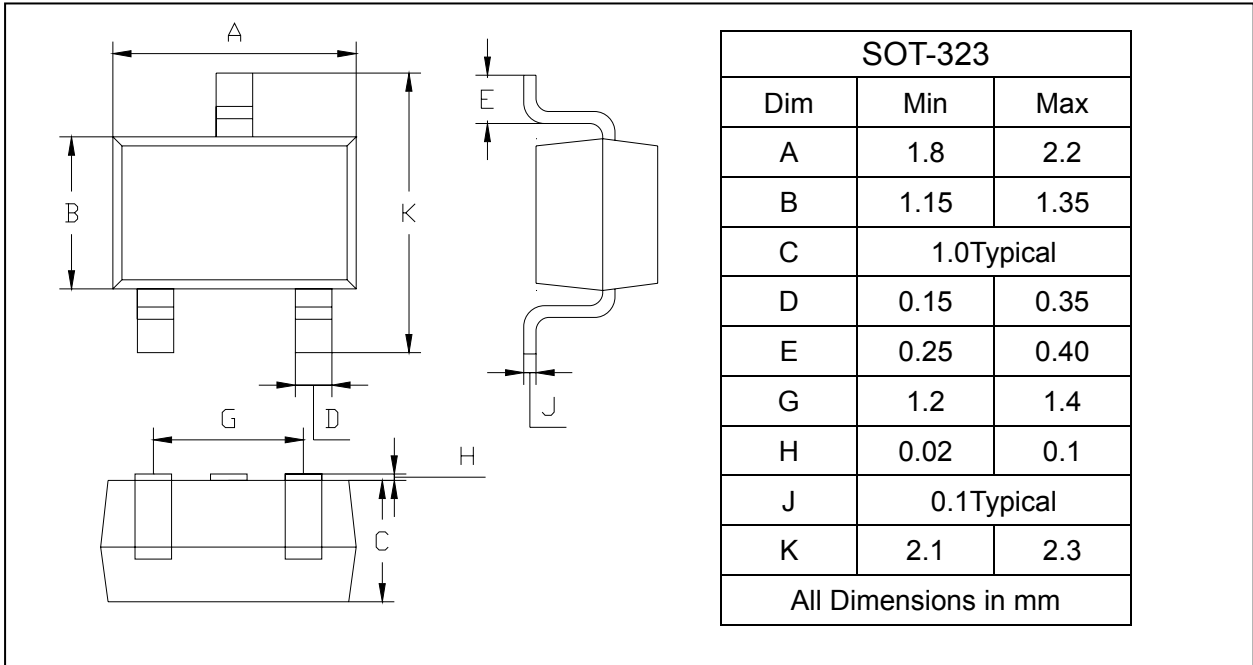
Surface Mount Schottky Barrier Diode

BAS70W/-04/-05/-06

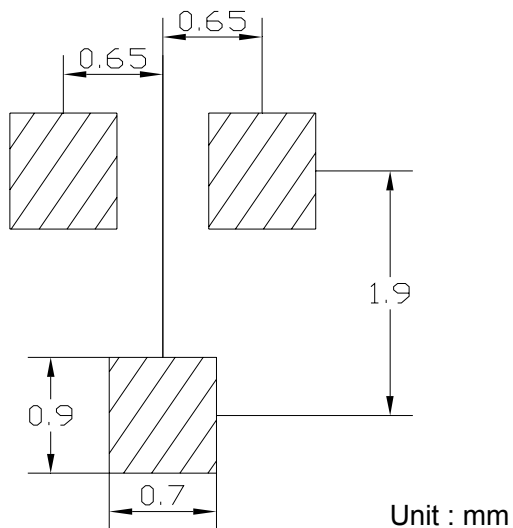
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAS70W/-04/-05/-06	SOT-323	3000/Tape&Reel